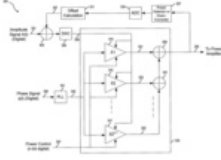
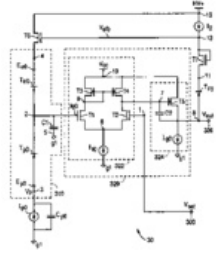
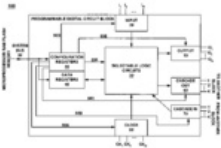
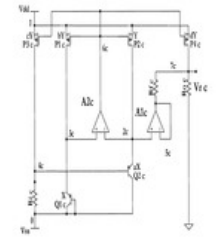
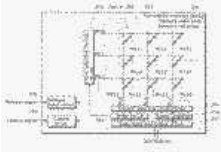
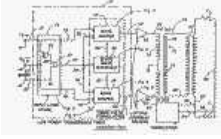
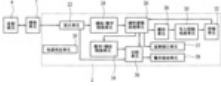


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#	Title	Publication number	Publ. date	Applicant/Assignee	
1.	Method and system for shared high-power transmit path for a multi-protocol transceiver	EP1931026	2008-06-11	AVAGO TECHNOLOGY INT SALES PTE LID AVAGO TECHNOLOGIES BROADCOM	
(EP1931053) Aspects of a method and system for a shared high-power transmit path for a multi-protocol transceiver are disclosed. Aspects of one method may include sharing a first power amplifier with a WLAN signal and a Bluetooth signal. The first power amplifier may amplify the WLAN signal and/or the Bluetooth signal simultaneously, or individually.					
2.	Analog floating gate voltage sense during dual conduction programming	WO2004/070987	2004-08-19	INTERMIL	
A method for sensing the voltage on a floating gate in a floating gate circuit during a set mode is disclosed. The method includes the steps of: a) causing the floating gate circuit (30) to enter into a set mode, wherein a first predetermined voltage (Vset) is coupled to the gate of a second transistor (T2) in the floating gate circuit; b) causing the voltage on the floating gate to be sensed relative to the first voltage by a first transistor (T1); c) causing an output voltage (Vout) to be generated by the floating gate circuit; and d) causing the voltage on the floating gate to be modified as a function of the output voltage, including modifying the charge level on said floating gate under the control of a first tunnel device (Te) and a second tunnel device (Tp) operating in dual conduction during said set mode, said first tunnel device formed between said floating gate and a first tunnel electrode (Ee) and said second tunnel device formed between said floating gate and a second tunnel electrode (Ep); and e) repeating steps b) through d) until the voltage on the floating gate is approximately equal to the first voltage.					
3.	Programming methodology and architecture for an analog programmable system on a chip	EP1202184	2002-05-02	MONTEREY RESEARCH MORGAN STANLEY SPANSION CYPRESS SEMICONDUCTOR	
A method of programming a programmable analog device architecture that introduces on a single chip a set of tailored analog blocks and elements that can be configured and reconfigured in different ways to implement a variety of different analog functions. The analog blocks can be electrically coupled to each other in different combinations to perform different analog functions. The architecture includes an array of analog blocks, including continuous time blocks and different types of switched capacitor blocks. Each analog block includes analog elements that have changeable characteristics that can be specified according to the function to be performed. Configuration registers define the type of function to be performed, the way in which the analog blocks are to be coupled, the inputs and outputs of the analog blocks, and the characteristics of the analog elements. The configuration registers can be dynamically programmed. Thus, the device can be used to realize a large number of different analog functions and applications.					
4.	Ultra-low power and ultra-low voltage bandgap voltage regulator device and method thereof	US9780652	2017-10-03	FAR ALI TASDIGHI	
A family of bandgap embodiments are disclosed herein, capable of operating with very low currents and low power supply voltages, using neither any custom devices nor any special manufacturing technology, and fabricated on mainstream standard digital CMOS processes. As such, manufacturing cost can be kept low, manufacturing yields of digital CMOS system-on-a-chip (SOC) that require a reference can be kept optimal, and manufacturing risk can be minimized due to its flexibility with respect to fabrication process node-portability. Although the embodiments disclosed herein use novel techniques to achieve accurate operations with low power and low voltage, this family of bandgaps also uses parasitic bipolar junction transistors (BJT) available in low cost digital CMOS process to generate proportional and complementary to absolute temperature (PTAT and CTAT) voltages via the base-emitter voltage (VEB) of BJTs and scaling VEB differential pairs to generate the BJTs thermal voltage (VT).					
5.	Nonvolatile memory element and nonvolatile memory device	WO2010/064446	2010-06-10	PANASONIC PANASONIC ELECTRIC INDUSTRY	
Provided is a nonvolatile memory element capable of stable resistance change operation at a low breakdown voltage. The nonvolatile memory element (100) is equipped with a first electrode layer (103), a second electrode layer (105), and a resistance change layer (104) which is between the electrode layers (103 and 105) and reversibly transitions between a high-resistance state and a low-resistance state based on the polarity of a voltage applied between the electrode layers (103 and 105). The resistance change layer (104) is configured by layering of a first oxide layer (104a) containing an oxide of a first transition metal and a second oxide layer (104b) containing an oxide of a second transition metal different from the first transition metal. The standard electrode potential of the second transition metal is lower than the standard electrode potential of the first transition metal, and at least either (1) the dielectric constant of the second oxide layer (104b) is higher than the dielectric constant of the first oxide layer (104a), or (2) the band gap of the second oxide layer (104b) is smaller than the band gap of the first oxide layer (104a) is satisfied.					
6.	All monolithic transceiver operative from a low voltage vcc dc supply.	EP0531474	1993-03-17	MEDTRONIC	
A new and improved all monolithic transceiver manufactured on a single semiconductor die and operative from a 5 volt DC power supply. The transceiver meets all of the pulse width and timing requirements of the MIL-STD-1553 transceiver and is operative at high switching speeds and high output current levels to generate bi-phase TX OUT and TX OUT signals used to drive, respectively, two center tapped primary windings of an output transformer. The transmitter includes two dynamically driven data channels which are driven out of phase and in a controlled manner that ensures that one data channel has been completely turned off before the other data channel turns on, thereby maximizing power transfer and operating efficiency while minimizing unnecessary current drain and eliminating current spiking in the output of the transmitter. The receiver of the transceiver includes a differential amplifier connected to drive first a balanced differential filter and then a differential window comparator which establish the bandwidth, voltage thresholds, gain-versus-frequency characteristic and Q point of the transceiver. Advantageously, the above all monolithic construction is facilitated by the use of MOS capacitor technology and by the use of chrome-silicon alloy technology to form, respectively, thin film capacitors and resistors on the surface of the monolithic die and used in the construction of resistor-capacitor filter networks, bias and load resistors, and the like. The above differential window comparator is connected to a pair of output logic drivers to generate therefrom RX DATA OUT and RX DATA OUT bi-phase output signals for use in controlling an associated computer.					
7.	Smoke measuring device and its critical value setting method and detecting method by using the same	CN101153844	2008-04-02	LIN JIANGBIAO	
The invention discloses a smoke detector, the method for setting the critical value of the detector and the detecting method during using the detector and aims to solve the problem existing in the prior art that quality disparity is caused by the error produced during making smoke detector by hand. The critical value of the smoke detector is set inside a memory unit in digital mode under identical testing environment during production, thereby avoiding the problems of error and quality disparity caused by hand operation; moreover, when used, the smoke detector compares outdoor smoke density with the critical value stored in the memory unit and outputs alarm signal to an alarm unit to remind a user whether a fire occurs.					